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1. (Previously Presented) A method of production of an ultra-thin semiconductor device comprising the steps of:

forming a first single crystalline semiconductor layer on a seed substrate via a first porous semiconductor peeling layer;

bonding said seed substrate from said first single crystalline semiconductor layer side in the state with an insulating layer interposed to a support substrate having a second single crystalline semiconductor layer formed thereon via a second porous semiconductor peeling layer wherein the first porous semiconductor peeling layer has a greater porosity than the second porous semiconductor peeling layer;

separating said seed substrate using said first porous semiconductor peeling layer as an interface; and

separating said support substrate using said second porous semiconductor peeling layer as an interface to obtain said first single crystalline semiconductor layer formed on said insulating layer.

84. (Previously Presented) A method of production of an ultra-thin semiconductor device comprising the steps of:

forming a first single crystalline semiconductor layer on a seed substrate via a first porous semiconductor peeling layer;

bonding said seed substrate from said first single crystalline semiconductor layer side in the state with an insulating layer interposed to a support substrate having a second single crystalline semiconductor layer formed thereon via a second porous semiconductor peeling layer wherein the first porous semiconductor peeling layer has a greater thickness than the second porous semiconductor peeling layer;

separating said seed substrate using said first porous semiconductor peeling layer as an interface; and

separating said support substrate using said second porous semiconductor peeling layer as an interface to obtain said first single crystalline semiconductor layer formed on said insulating layer.